

IBIS Modeling Using Latency Insertion Method (LIM)

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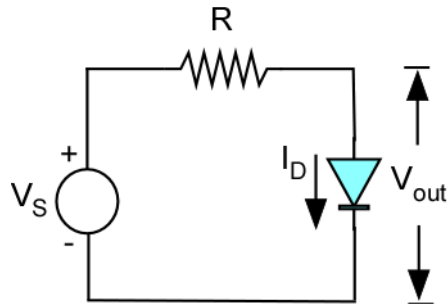
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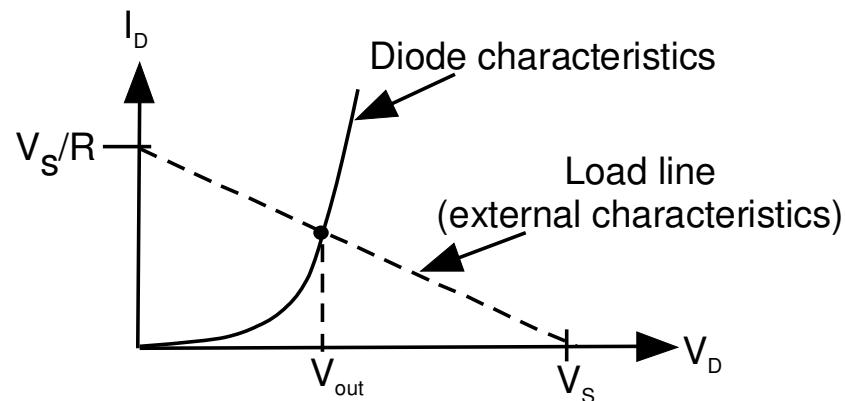


Nonlinear Circuit



How do we solve a simple diode circuit problem?

Graphical method... ... solve transcendental equations



$$V_{out} = V_D$$

$$I_D = I_S \left(e^{V_D/V_T} - 1 \right)$$

$$V_S = RI_D + V_D = RI_D(V_D) + V_D$$



Diode Circuit – Iterative Method

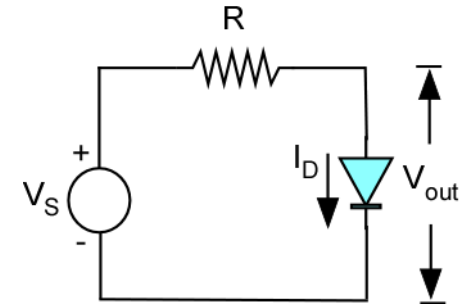
... or use the **Newton-Raphson method**...

Use: $x_{k+1} = x_k - [f'(x_k)]^{-1} f(x_k)$

$$V_{out} = V_D$$

$$x^{(k+1)} = x^{(k)} - [f'(x^{(k)})]^{-1} f(x^{(k)})$$

$$f(V_D) = \frac{V_D - V_S}{R} + I_S (e^{V_D/V_T} - 1) = 0 \quad f'(V_D) = \frac{1}{R} + \frac{I_S}{V_T} e^{V_D/V_T}$$



$$V_D^{(k+1)} = V_D^{(k)} - \frac{\frac{V_D^{(k)} - V_S}{R} + I_S (e^{V_D^{(k)}/V_T} - 1)}{\frac{1}{R} + \frac{I_S}{V_T} e^{V_D^{(k)}/V_T}}$$

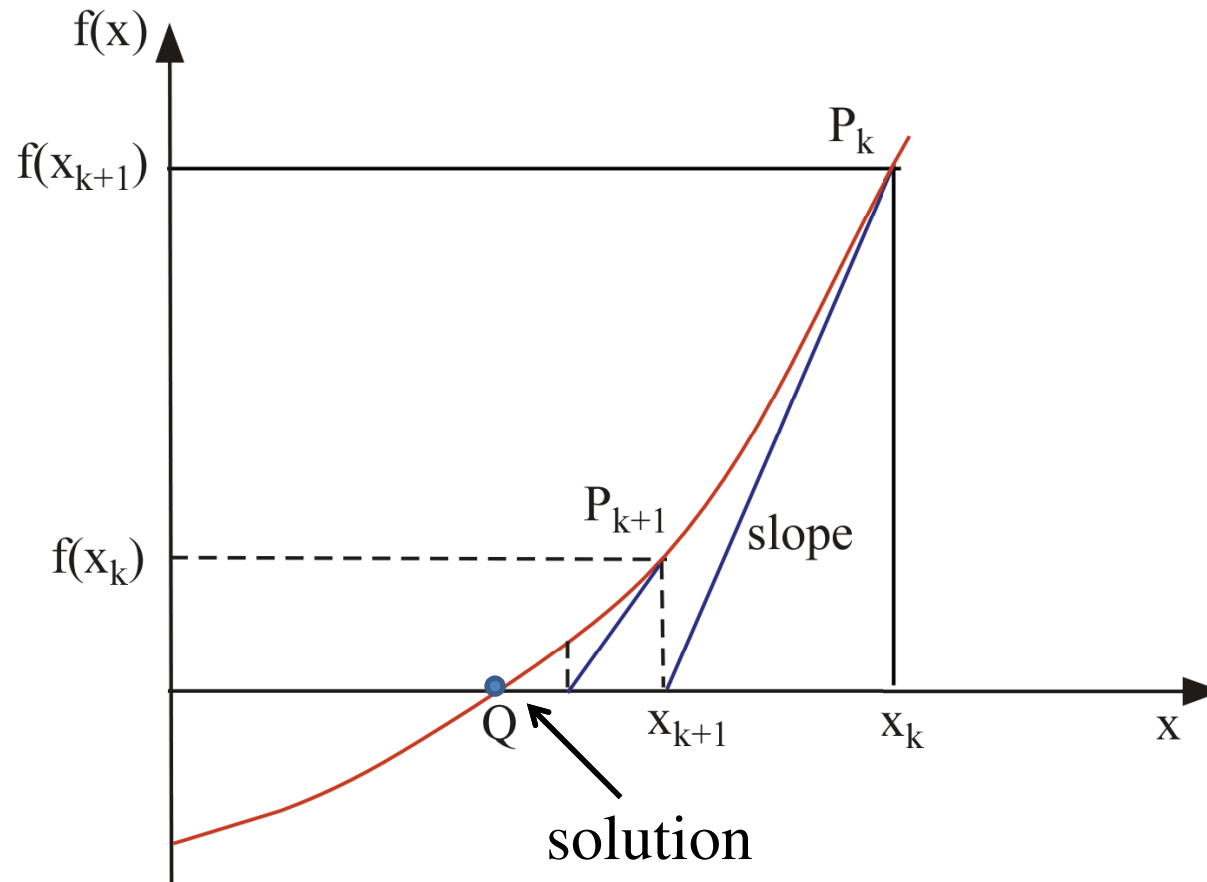
Where $V_D^{(k)}$ is the value of V_D at the k th iteration

Procedure is repeated until convergence to final (true) value of V_D which is the solution. Rate of convergence is quadratic.



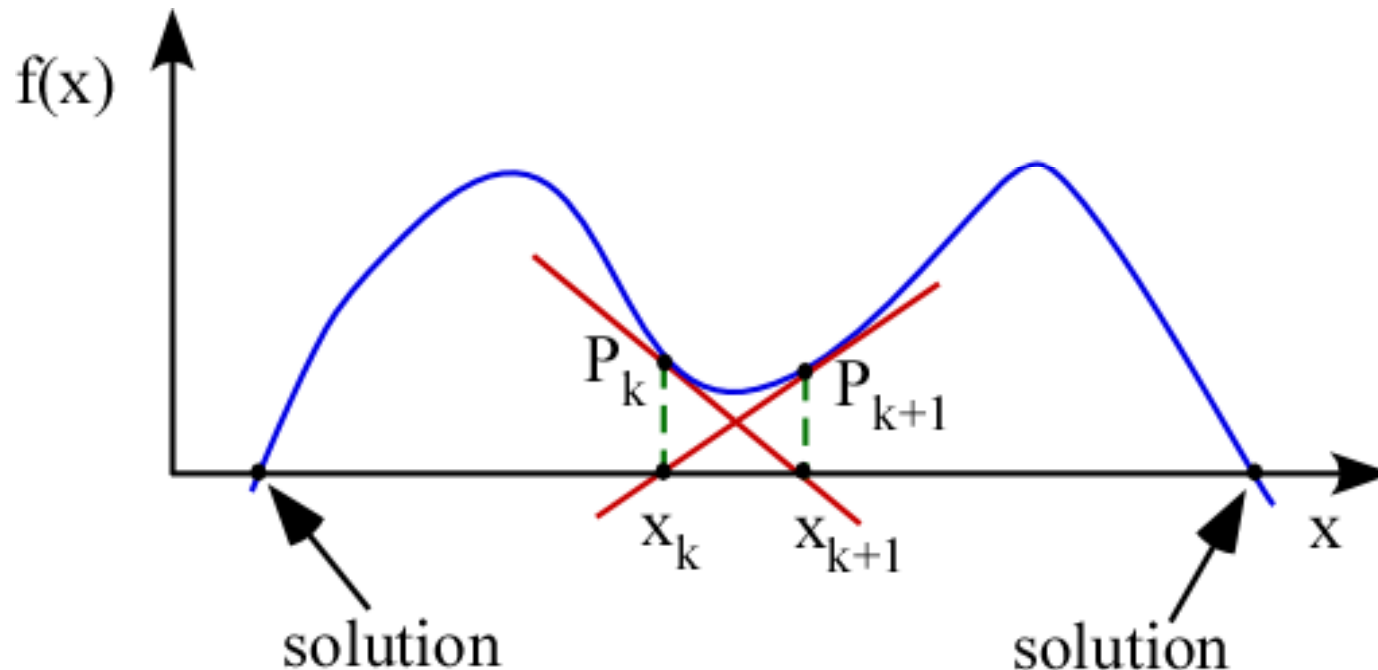
Newton Raphson Method

(Graphical Interpretation)



Newton Raphson Method

If initial guess is not close enough, NR will lock into oscillations and solution will not converge



Limitations

- IBIS data can be unpredictable
- Transient response requires solution of nonlinear system
- Most simulators use Newton-Raphson (NR) technique combined with modified nodal analysis (MNA)
- NR may not converge
- NR may slow down simulation



Why LIM?

- LIM does not iterate on nonlinear problems
- There is no convergence issue
- MNA has super-linear numerical complexity
- LIM has linear numerical complexity
- LIM uses no matrix formulation
- LIM has no matrix ill-conditioning problems
- LIM is much faster than MNA for large circuits



Latency Insertion Method**

Each branch must have an inductor*

Each node must have a shunt capacitor*

Express branch current in terms of history of adjacent node voltages

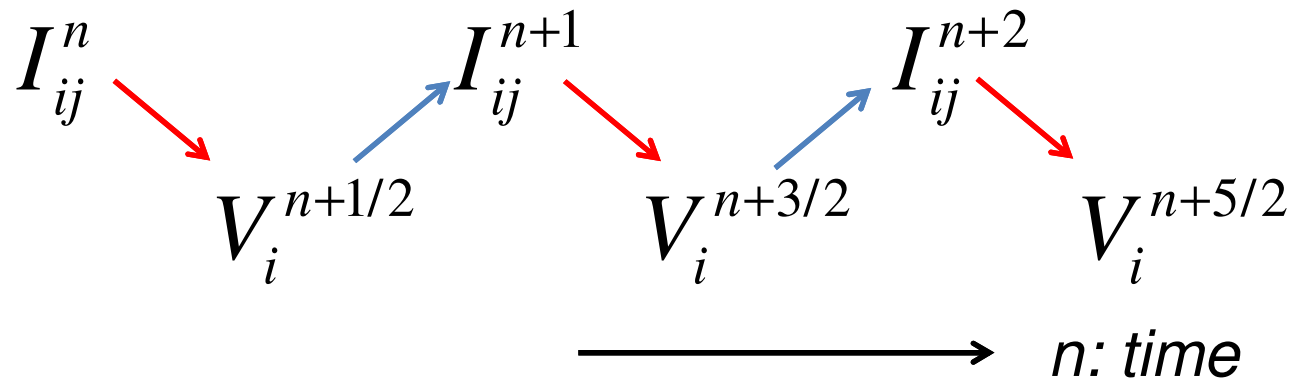
Express node voltage in terms of history of adjacent branch currents

** If branch or node has no inductor or capacitor, insert one with very small value*

** J. E. Schutt-Ainé, "Latency Insertion Method for the Fast Transient Simulation of Large Networks," IEEE Trans. Circuit Syst., vol. 48, pp. 81-89, January 2001.



LIM: Leapfrog Method



$$V_i^{n+1/2} = \frac{\frac{C_i V_i^{n-1/2}}{\Delta t} + H_i^n - \sum_{k=1}^{N_a} I_{ik}^n}{\frac{C_i}{\Delta t} + G_i}$$

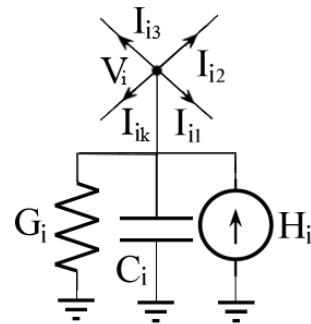
$$I_{ij}^{n+1} = I_{ij}^n + \frac{\Delta t}{L_{ij}} (V_i^{n+1/2} - V_j^{n+1/2} - R_{ij} I_{ij}^n)$$

Leapfrog method achieves second-order accuracy, i.e., error is proportional to Δt^2

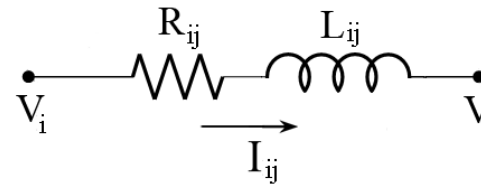


LIM Algorithm

- Represents network as a grid of nodes and branches



Node structure



Branch structure

- Discretizes Kirchhoff's current and voltage equations

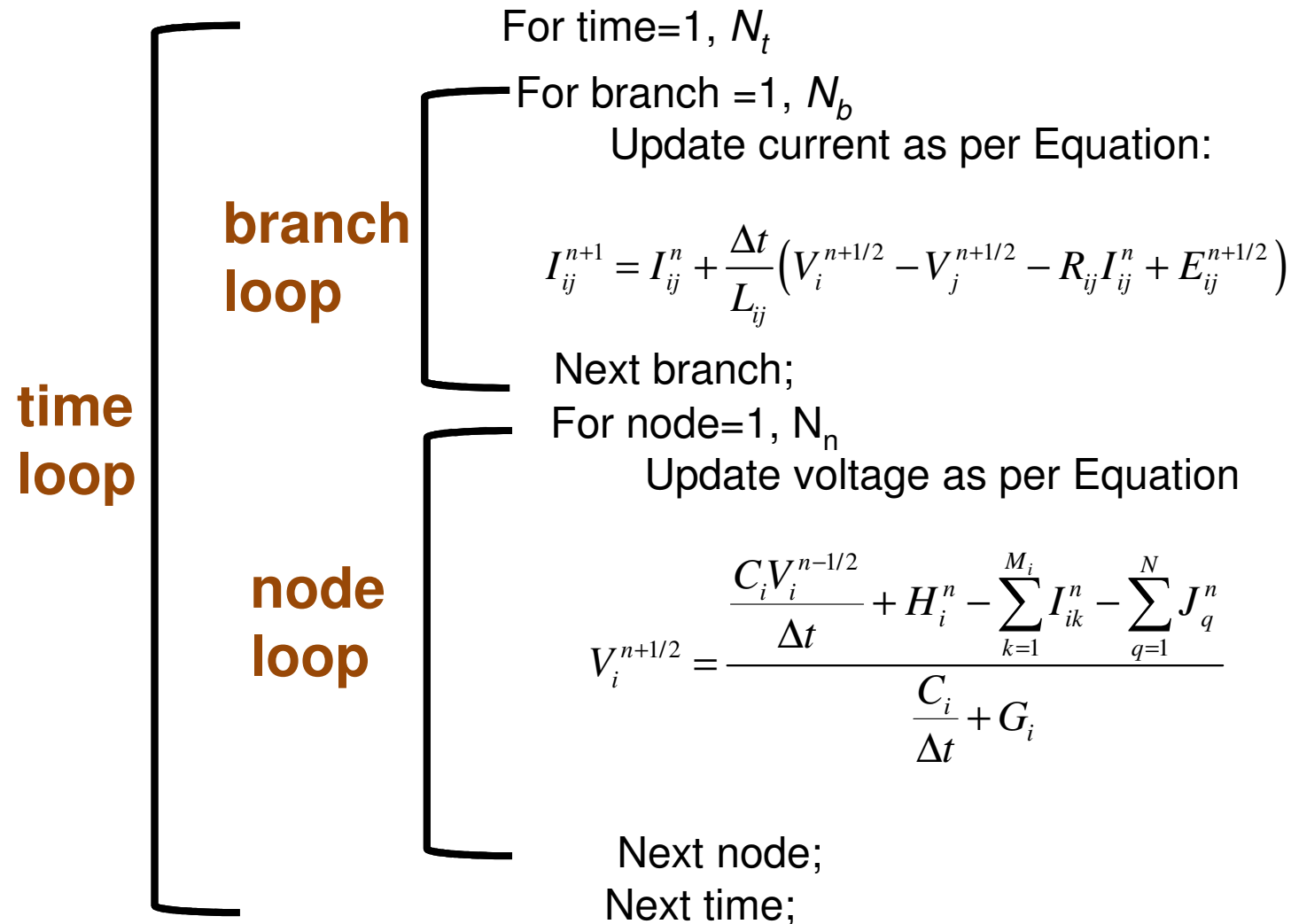
$$V_i^{n+1/2} = \frac{\frac{C_i V_i^{n-1/2}}{\Delta t} + H_i^n - \sum_{k=1}^{N_a} I_{ik}^n}{\frac{C_i}{\Delta t} + G_i}$$

$$I_{ij}^{n+1} = I_{ij}^n + \frac{\Delta t}{L_{ij}} (V_i^{n+1/2} - V_j^{n+1/2} - R_{ij} I_{ij}^n)$$

- Uses "leapfrog" scheme to solve for node voltages and branch currents
- Presence of reactive elements is required to generate latency



LIM is Easy to Code...



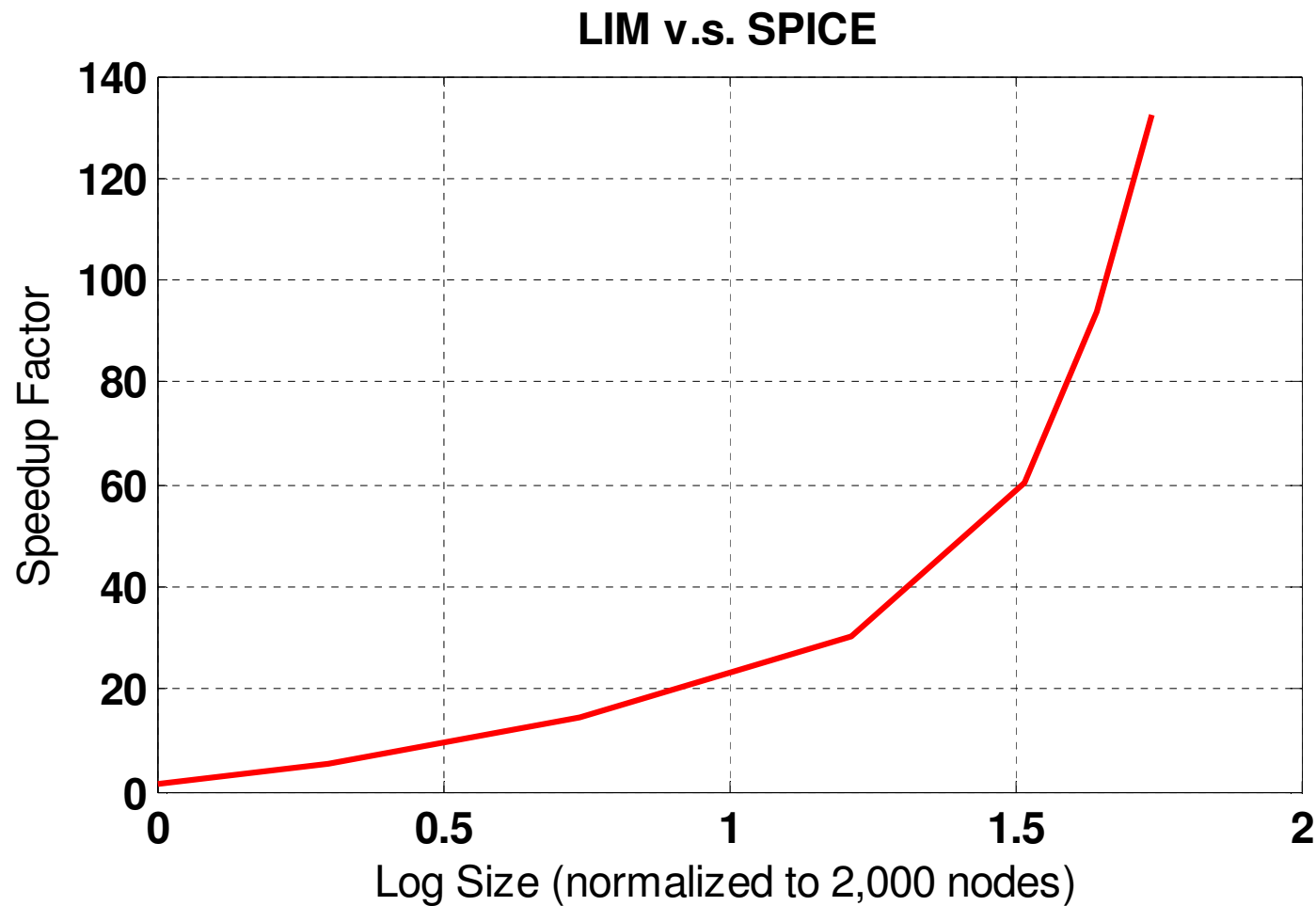
LIM is Fast...

Comparison of runtime for LIM and SPICE
per 100 time steps.

Circuit	# nodes	# MOSFET	SPICE	LIM
ADDER	36	62	0.0058 s	0.0005 s
VOTER	1709	4243	0.369 s	0.041 s
RAM CKT	4850	13880	1.94 s	0.184 s



... and gets faster as circuit size increases



LIM has NO Convergence Issues

Introduce latency in diode circuit
through a small inductor L

... then use collocation and leapfrog:

$$V_D \rightarrow V_D^n, V_D^{n+1}, V_D^{n+2}, \dots$$

$$I_D \rightarrow I_D^{n-1/2}, I_D^{n+1/2}, I_D^{n+3/2}, \dots \quad \text{with} \quad V_L^n = L \frac{I^{n+1/2} - I^{n-1/2}}{\Delta t}$$

...and if time steps are sufficiently small,

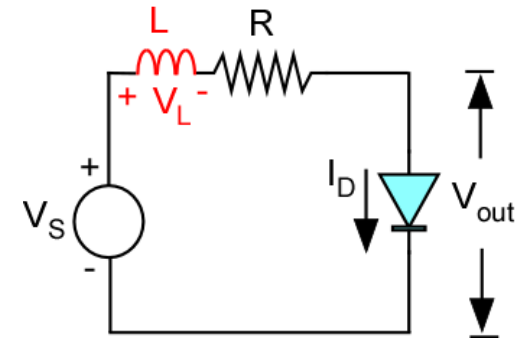
Current
solution

$$I_D^{n+1/2} = I_S \left(e^{V_D^n / V_T} - 1 \right)$$

or

Voltage
solution

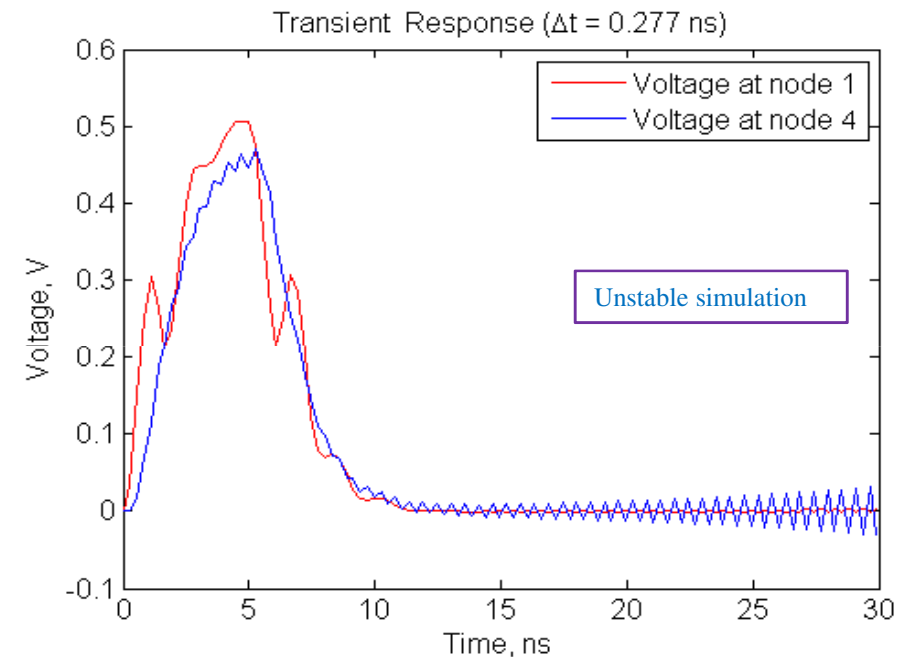
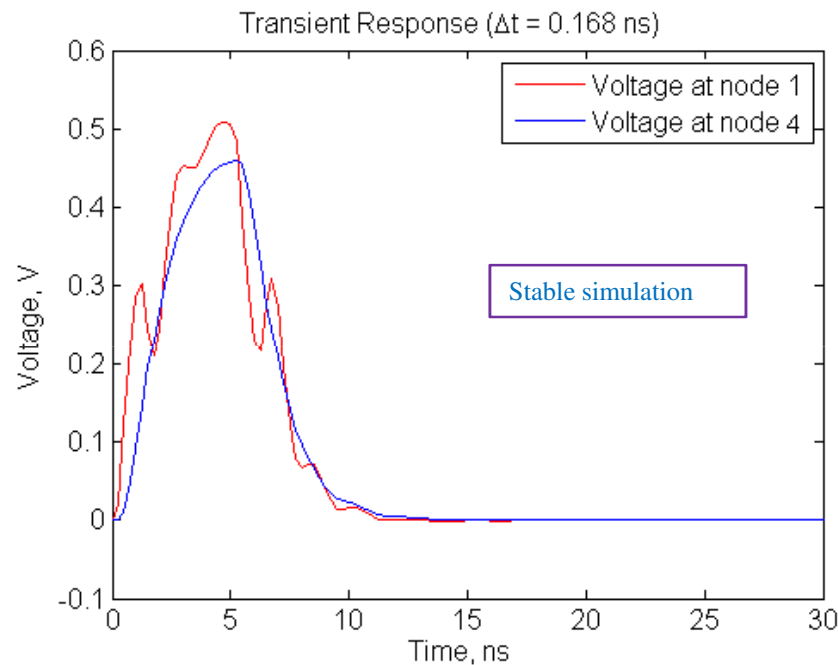
$$V_D^{n+1} = V_T \ln \left(\frac{I_D^{n+1/2}}{I_S} + 1 \right)$$



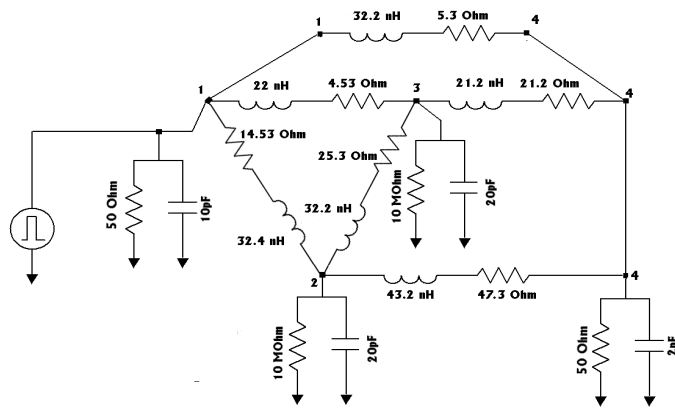
Explicit !



LIM Suffers from Stability Issues ...



...but they can be controlled...

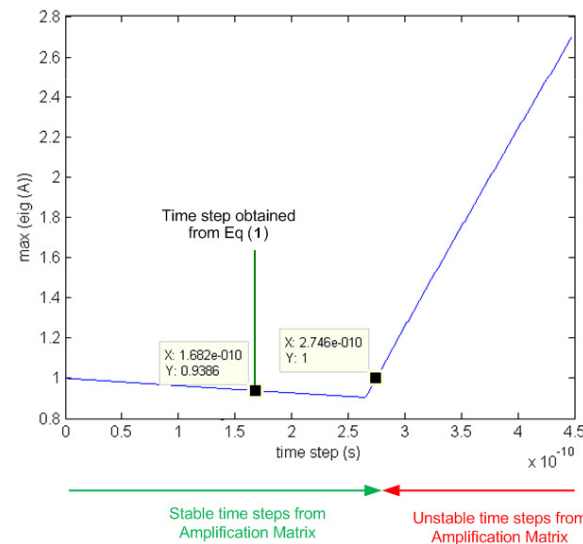
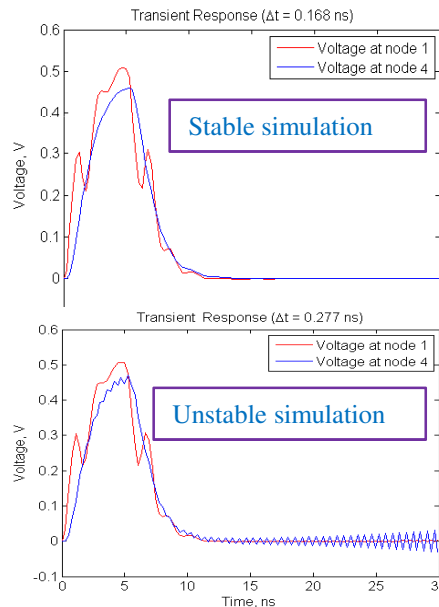


- The LIM algorithm is conditionally stable
- No faster than speed of light propagation

➤ The Amplification Matrix [5]

- Eigenvalues must be less than unity for the system to be stable
- A-matrix provides the exact limit on the size of the time step

$$\begin{bmatrix} \mathbf{v}^{n+1/2} \\ \mathbf{i}^{n+1} \end{bmatrix} = \mathbf{A} \begin{bmatrix} \mathbf{v}^{n-1/2} \\ \mathbf{i}^n \end{bmatrix}$$



➤ The Energy Method [6]

$$\Delta t \leq \sqrt{2} \min_{i=1}^{N_n} \left(\sqrt{\frac{C_i}{N_b^i} \min_{p=1}^{N_b^i} (L_{i,p})} \right)$$

- Smallest LC product in the circuit
- Provides a sufficient condition on Δt
- Easy to use in our simulations



Application of LIM to IBIS

- IBIS Data Processing
- Ku/Kd Extraction
- IBIS Standard Formulation
- LIM-IBIS Formulation
- LIM-IBIS Solutions
- Extension to Gate Modulation Effects
- Conclusion and Future Work



IBIS Data Processing

1. Arrange static IV data
2. Pulldown data (current vs voltage) $\rightarrow I_{pd}, m_{pd}$ points
3. Pullup data (current vs voltage) $\rightarrow I_{pu}, m_{pu}$ points
4. Ground clamp data (current vs voltage) $\rightarrow I_{gc}, m_{gc}$ points
5. Power clamp data (current vs voltage) $\rightarrow I_{pc}, m_{pc}$ points

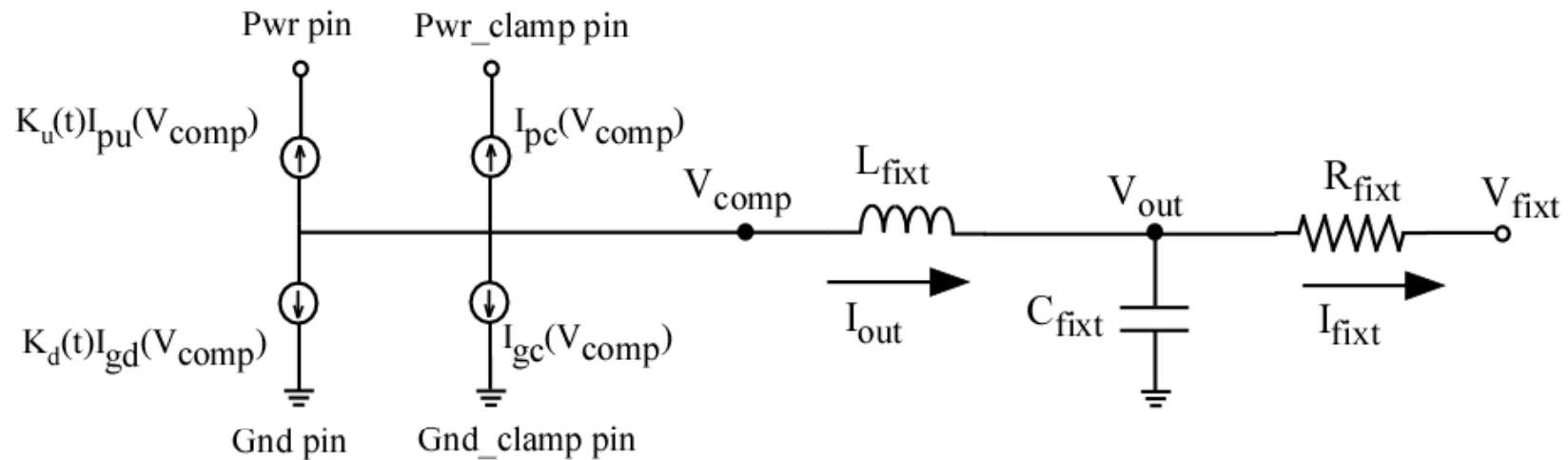


IBIS Data Processing

- Next Get VT data. VT data is presented as: Rising waveform:
- Voltage versus time for V_{fix} low $\rightarrow V_{R1}, m_{r1}$ points
- Voltage versus time for V_{fix} high $\rightarrow V_{R2}, m_{r2}$ points: Falling waveform:
- Voltage versus time for V_{fix} low $\rightarrow V_{F1}, m_{f1}$ points
- Voltage versus time for V_{fix} high $\rightarrow V_{F2}, m_{f2}$ points



IBIS Ku/Kd Extraction*



$$I_{fixt} = \frac{V_{out} - V_{fixt}}{R_{fixt}}$$

$$I_{cap} = C_{fixt} \frac{V_{out}(t) - V_{out}(t - \Delta t)}{\Delta t}$$

$$V_{comp} = L_{fixt} \frac{\Delta I_{out}}{\Delta t} + V_{out}$$

$$I_{out} = I_{cap} + I_{fixt}$$



Ku/Kd Extraction

We need to extract K_u and K_d

Procedure is well documented*

- Pick value V_{comp1}
- Find closest corresponding currents in static IV data
- Set them as I_{pd1} , I_{pu1} , I_{gc1} and I_{pc1}
- Pick value V_{comp2}
- Find closest corresponding currents in static IV data
- Set them as I_{pd2} , I_{pu2} , I_{gc2} and I_{pc2}

* Ying Wang, Han Ngee Tan "The Development of Analog SPICE Behavioral Model Based on IBIS Model", Proceedings of the Ninth Great Lakes Symposium on VLSI, GLS '99.



IBIS Circuit Analysis

2 equations, two unknown system

$$-I_{out1} = K_u I_{pu1} + K_d I_{pd1} + I_{pc1} + I_{gc1}$$

$$-I_{out2} = K_u I_{pu2} + K_d I_{pd2} + I_{pc2} + I_{gc2}$$

Rearrange as:

$$K_u I_{pu1} + K_d I_{pd1} = -I_{out1} - I_{pc1} - I_{gc1} = I_{RHS1}$$

$$K_u I_{pu2} + K_d I_{pd2} = -I_{out2} - I_{pc2} - I_{gc2} = I_{RHS2}$$

or

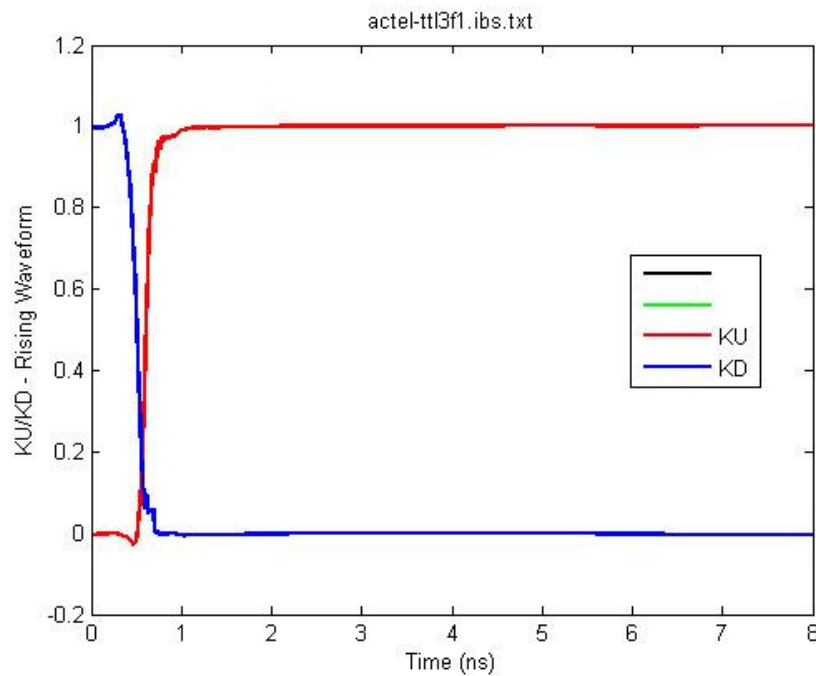
$$\begin{bmatrix} I_{pu1} & I_{pd1} \\ I_{pu2} & I_{pd2} \end{bmatrix} \begin{bmatrix} K_u \\ K_d \end{bmatrix} = \begin{bmatrix} I_{RHS1} \\ I_{RHS2} \end{bmatrix}$$

Solve for
 K_u and K_d

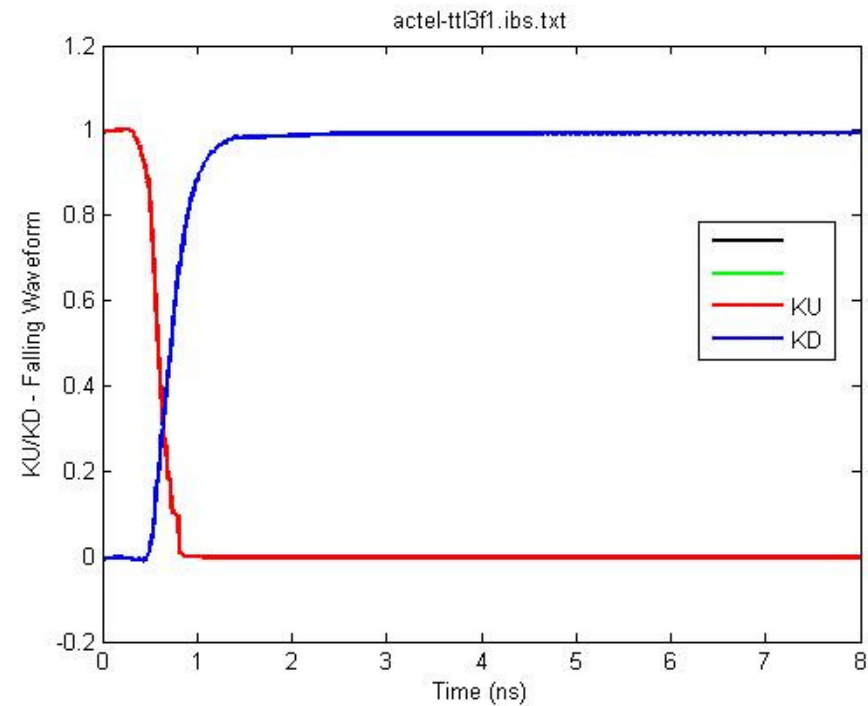


Example of Ku and Kd

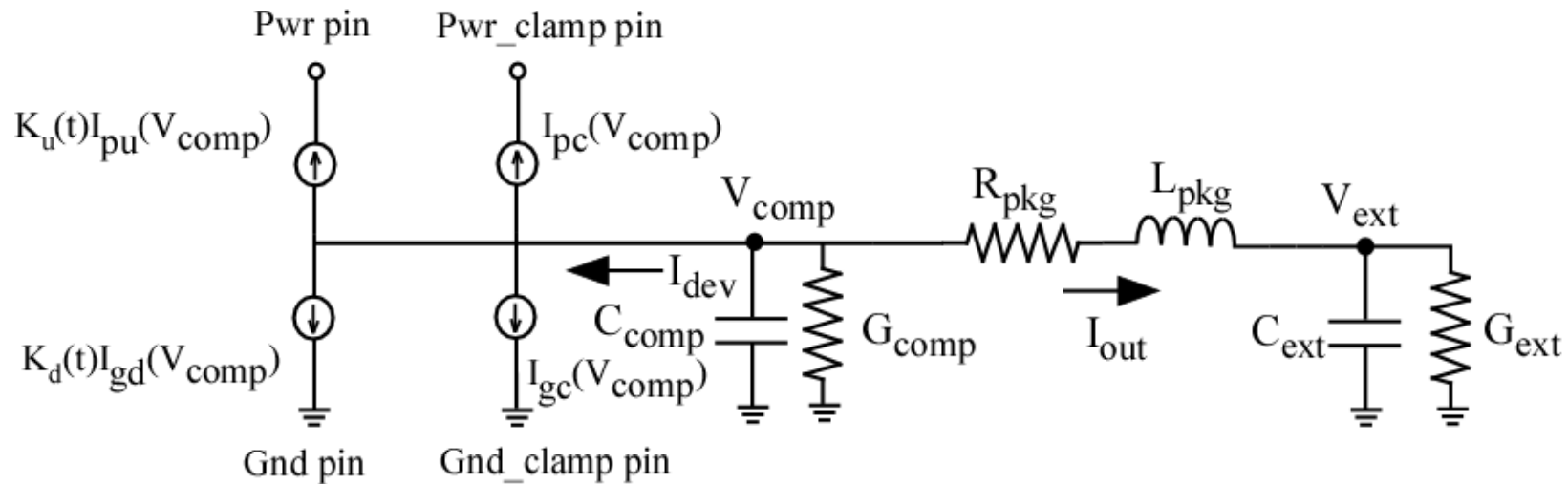
Rising Waveform



Falling Waveform



IBIS Simulations



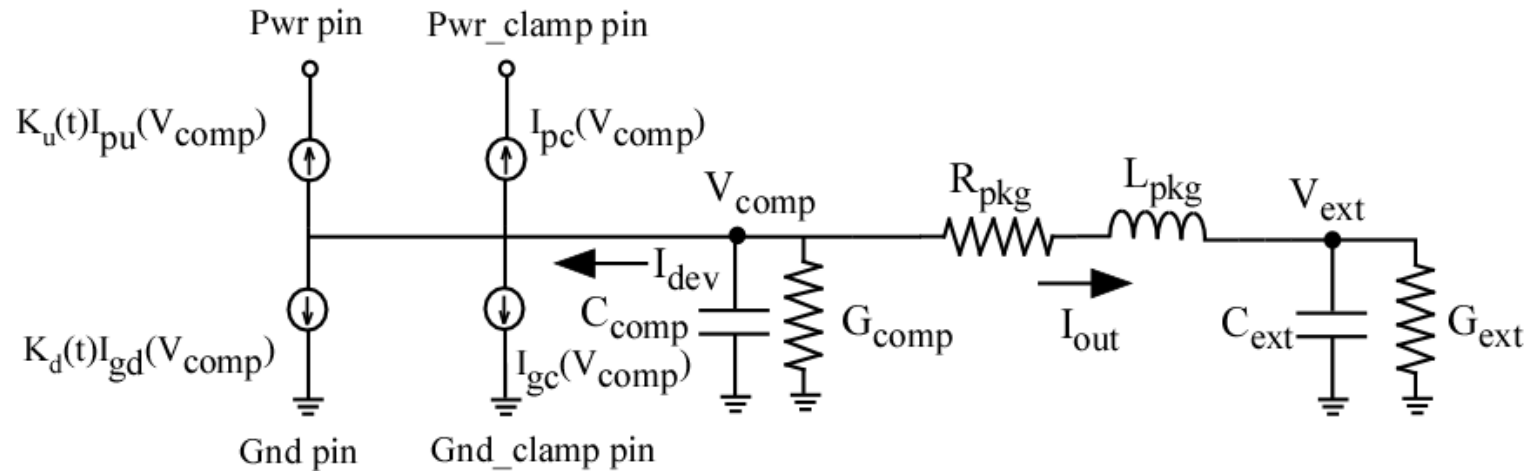
$$K_u I_{pu} (V_{comp}) + K_d I_{pd} (V_{comp}) + I_{pc} (V_{comp}) + I_{gc} (V_{comp})$$

$$+ I_{out} (V_{comp}) + I_{C_{comp}} (V_{comp}) + I_{G_{comp}} (V_{comp}) = 0$$

Nonlinear system → use Newton-Raphson



...or Better: Use a LIM Formulation



$$C_{ext} \frac{(V_{ext}^{n+1/2} - V_{ext}^{n-1/2})}{\Delta t} + \frac{G_{ext}}{2} (V_{ext}^{n+1/2} + V_{ext}^{n-1/2}) = I_{out}^n$$

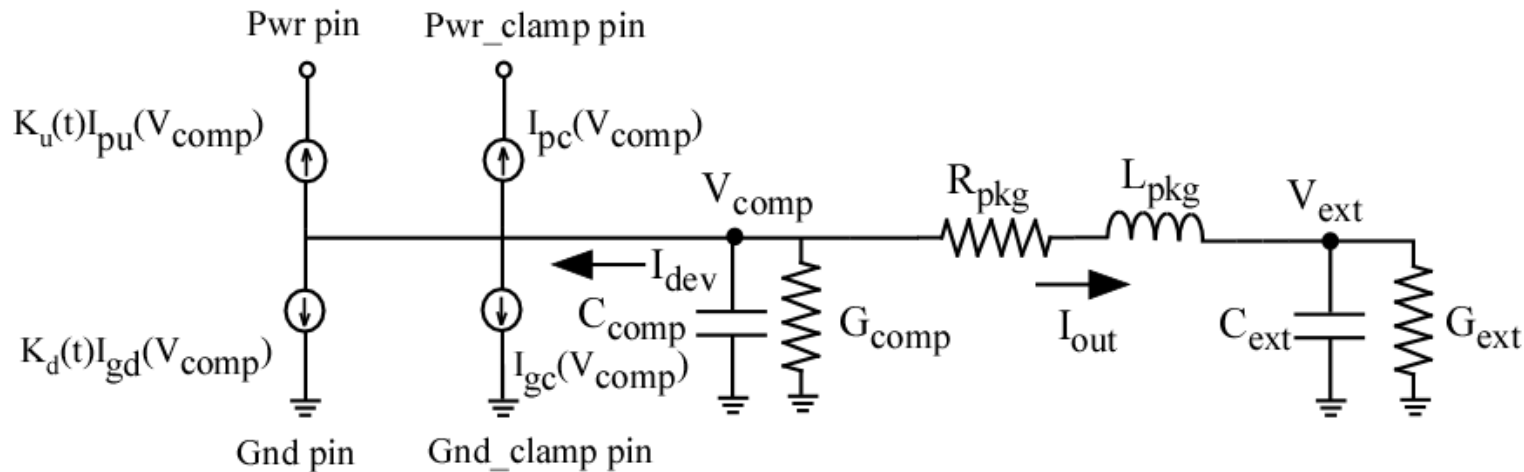
$$V_{ext}^{n+1/2} = \frac{I_{out}^n + \left(\frac{C_{ext}}{\Delta t} - \frac{G_{ext}}{2} \right) V_{ext}^{n-1/2}}{\left(\frac{C_{ext}}{\Delta t} + \frac{G_{ext}}{2} \right)}$$

$$V_{comp}^{n+1/2} - V_{ext}^{n+1/2} = L_{pkg} \frac{(I_{out}^{n+1} - I_{out}^n)}{\Delta t} + \frac{R_{pkg}}{2} (I_{out}^{n+1} + I_{out}^n)$$

$$I_{out}^{n+1} = \frac{(V_{comp}^{n+1/2} - V_{ext}^{n+1/2}) + I_{out}^n \left(\frac{L_{pkg}}{\Delta t} - \frac{R_{pkg}}{2} \right)}{\left(\frac{L_{pkg}}{\Delta t} + \frac{R_{pkg}}{2} \right)}$$



IBIS-LIM Solution



$$C_{comp} \frac{(V_{comp}^{n+1/2} - V_{comp}^{n-1/2})}{\Delta t} + \frac{G_{comp}}{2} (V_{comp}^{n+1/2} + V_{comp}^{n-1/2}) = -I_{out}^n - I_{dev}^n$$

$$V_{comp}^{n+1/2} = \frac{-I_{out}^n - I_{dev}^n + \left(\frac{C_{comp}}{\Delta t} - \frac{G_{comp}}{2} \right) V_{comp}^{n-1/2}}{\left(\frac{C_{comp}}{\Delta t} + \frac{G_{comp}}{2} \right)}$$

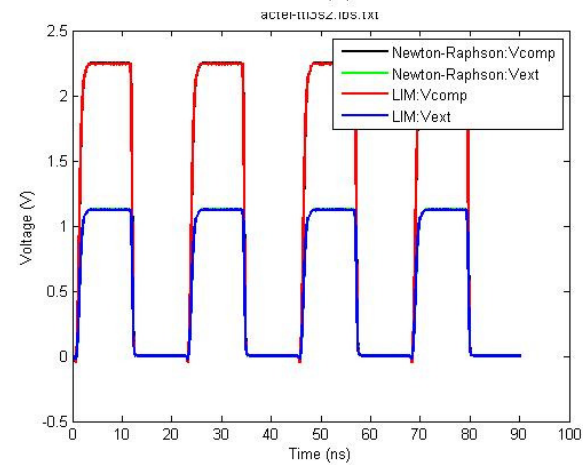
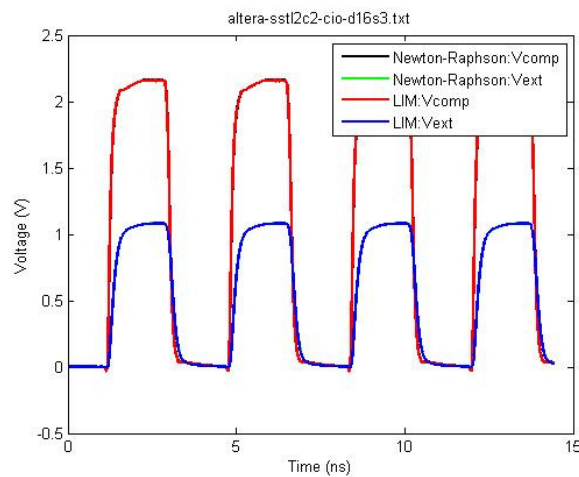
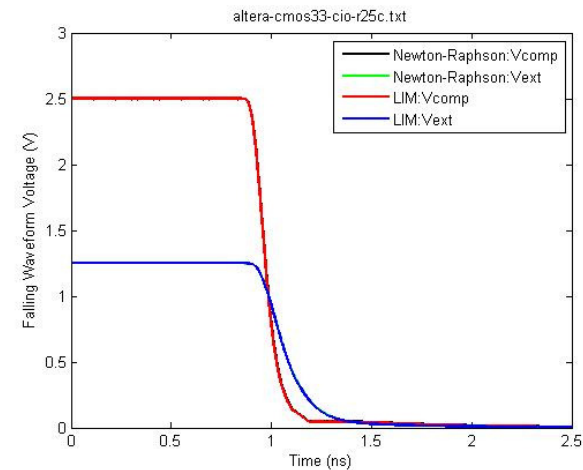
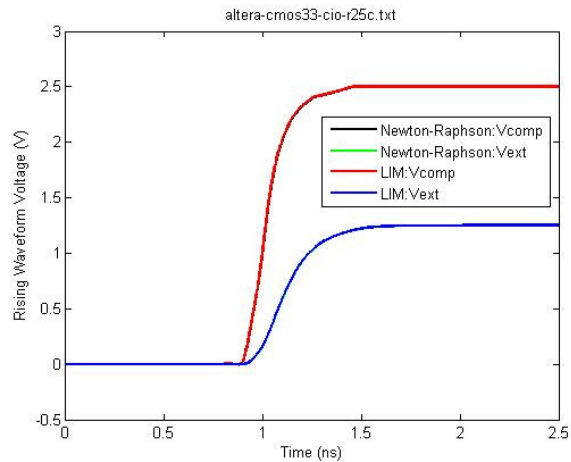
$$I_{dev}^n = K_u I_{pu}(V_{comp}) + K_d I_{pd}(V_{comp}) + I_{pc}(V_{comp}) + I_{gc}(V_{comp})$$

Explicit equations



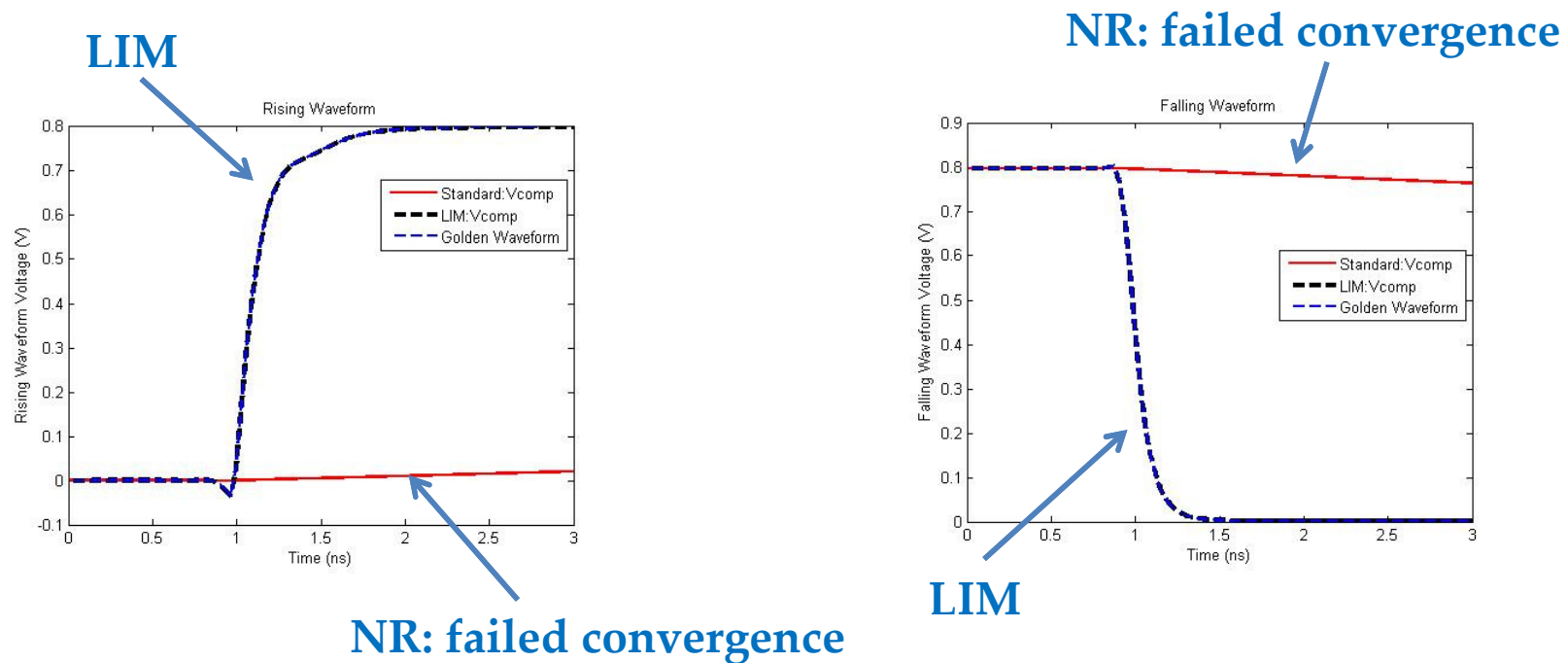
Transient Simulation Examples

NR and LIM give same results...



Transient Simulation Examples

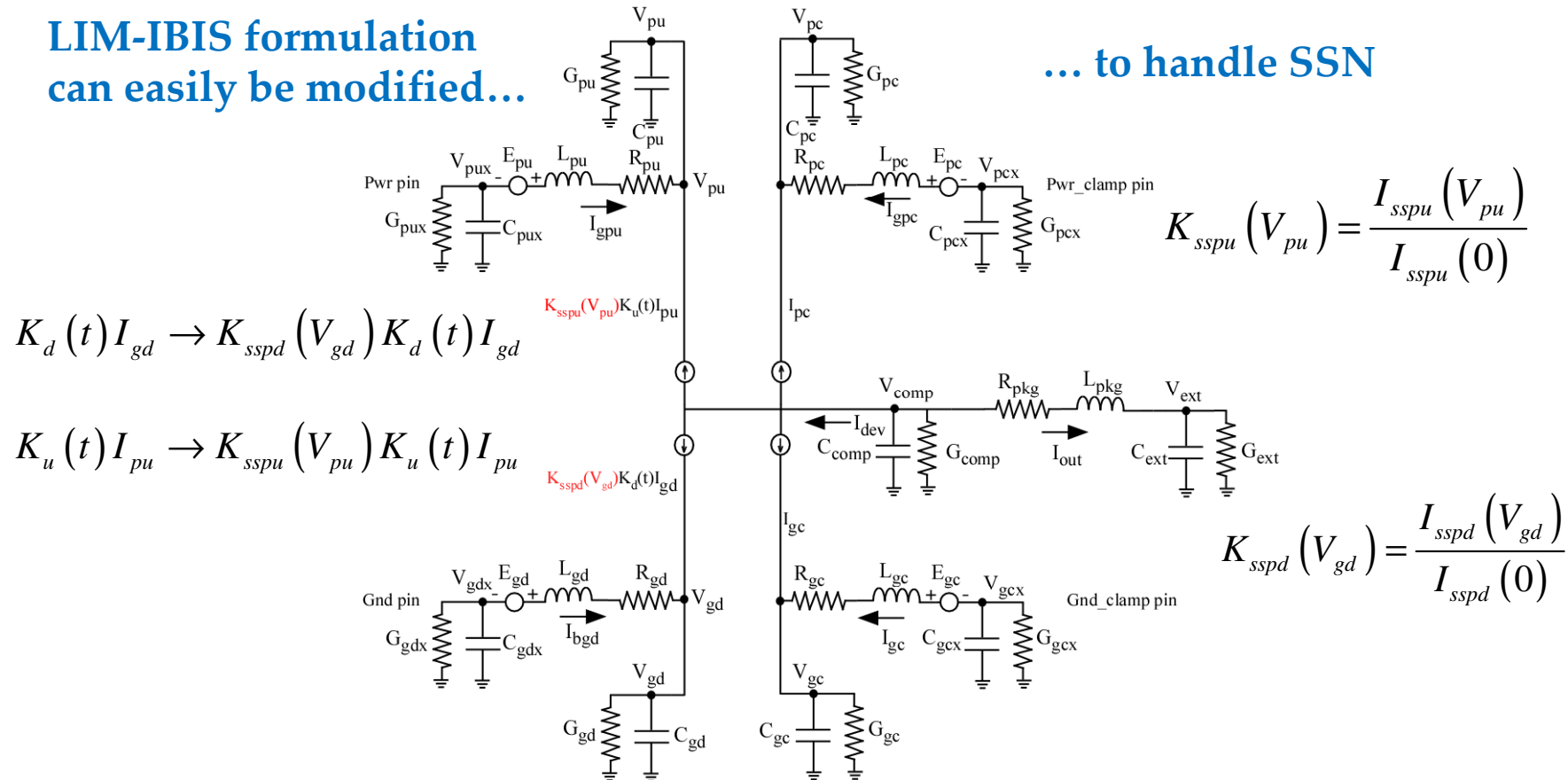
... in some cases Newton-Raphson fails to converge...



Handling Gate Modulation Effects (BIRD 98.3)

LIM-IBIS formulation
can easily be modified...

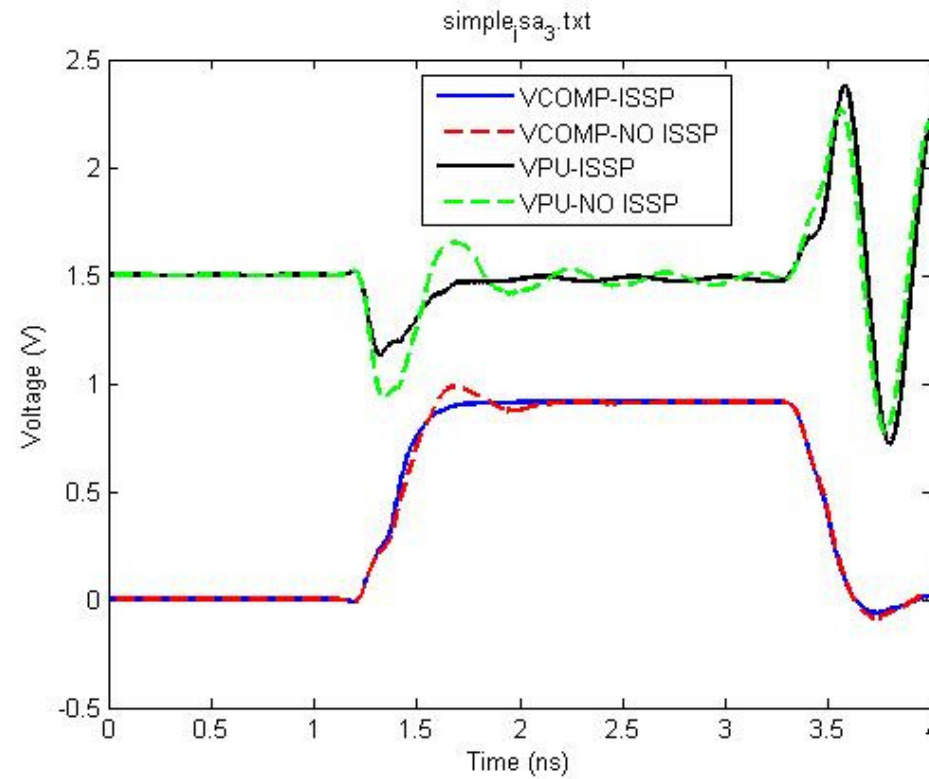
... to handle SSN



Gate Modulation Effects (BIRD 98.3)

Large power
supply inductance
Small decoupling
capacitance

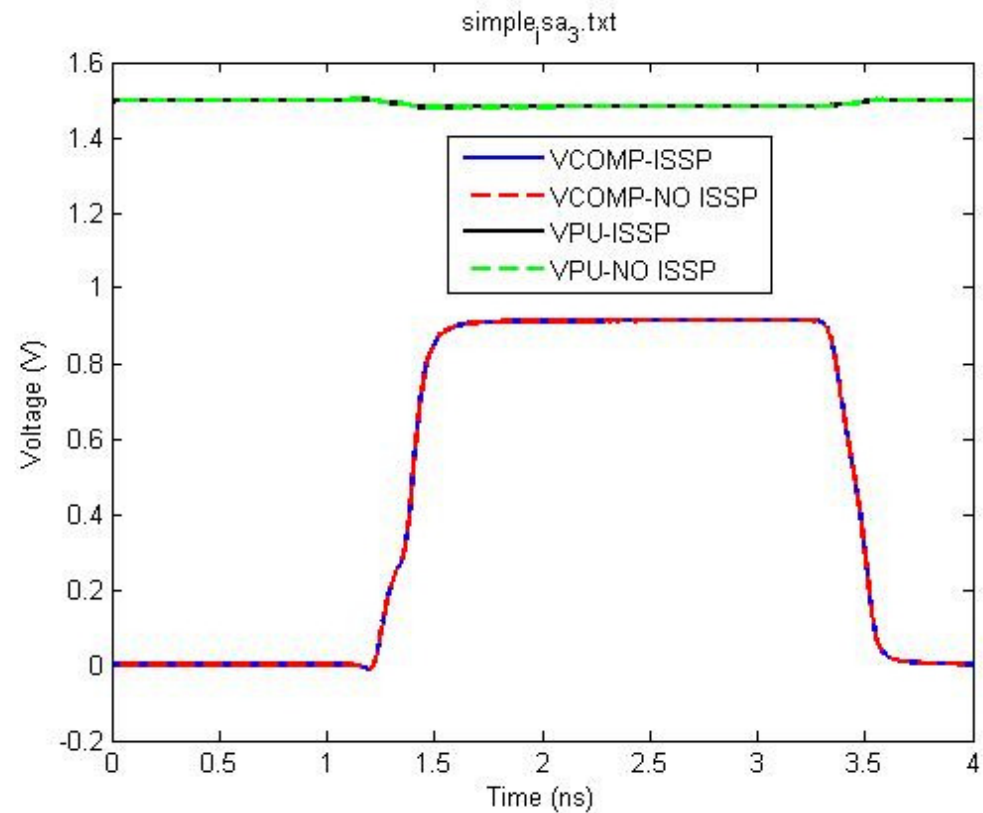
$$L_{pu} = 5 \text{ nH}$$
$$C_{pu} = 0.001 \text{ nF}$$



Gate Modulation Effects (BIRD 98.3)

Small power
supply inductance
Large decoupling
capacitance

$$L_{pu} = 0.005 \text{ nH}$$
$$C_{pu} = 0.1 \text{ nF}$$



Conclusions

- We demonstrated that LIM can be used to simulate IBIS-based circuits with optimum accuracy.
- Because of the inserted latency, LIM does not use an iterative scheme to solve nonlinear equations and thus does not suffer from convergence problems
- LIM-based simulations were successful in instances where the traditional Newton-Raphson technique failed to provide a solution
- LIM is expected to be several orders of magnitude faster for large circuits containing a multitude of IBIS models.



References

- [1] J. E. Schutt-Ainé, "Latency Insertion Method for the Fast Transient Simulation of Large Networks," *IEEE Trans. Circuit Syst.*, vol. 48, pp. 81-89, January 2001.
- [2] Dmitri Klokotov, and José Schutt-Ainé, "Transient Simulation of Lossy Interconnects using the Latency Insertion Method (LIM)", *Proceedings of the 17th Topical Meeting on Electrical Performance of Electronic Packaging (EPEP)*, pp. 251-254, San Jose, CA, October 2008.
- [3] José Schutt-Ainé, "Stability Analysis of the Latency Insertion Method Using a Block Matrix Formulation", *Proceedings of EDAPS-08*, Seoul, South Korea, December 2008.
- [4] J. Schutt-Ainé, D. Klokotov, P. Goh, Jilin Tan, F. Al-Hawari, Ping Liu, Wenliang Dai, "Application of the latency insertion method to circuits with blackbox macromodel representation," *Proceedings of the 11th Electronics Packaging Technology Conference (EPTC)*, pp. 92-95, Singapore, December 2009.
- [5] P. Goh, J. Schutt-Ainé, D. Klokotov, J. Tan, P. Liu, W. Dai, and F. Al-Hawari, "Partitioned latency insertion method with a generalized stability criteria," *IEEE Trans. on Comp., Packaging and Manufacturing Tech.*, vol. 1, no. 9, Sept. 2011.
- [6] S. Lalgudi and M. Swaminathan, "Analytical stability condition of the latency insertion method for nonuniform GLC circuits," *IEEE Trans. on Circuits and Systems*, vol. 55, no. 9, Sept. 2008.
- [7] Ying Wang, Han Ngee Tan "The Development of Analog SPICE Behavioral Model Based on IBIS Model", *Proceedings of the Ninth Great Lakes Symposium on VLSI, GLS '99*.
- [8] P. Tehrani, Y. Chen, and J. Fang, "Extraction of Transient Behavioral Model of Digital I/O Buffers from IBIS," *Proceedings of 1996 ECTC Conference*, pp1009-1015.

